

Low-frequency noise in focal plane array 640×512 InSb detectors

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The paper considers the regularities of low-frequency noise in large-format InSb FPA of the mid-infrared range and its influence on the quality of thermal imaging after inhomogeneity correction. It is found that low-frequency noise is less in the manufacture of photodetectors from indium antimonide ingots with increased impurity concentration.

Keywords: Focal Plane Array (FPA), low-frequency noise, photodiode matrix, indium antimonide.

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